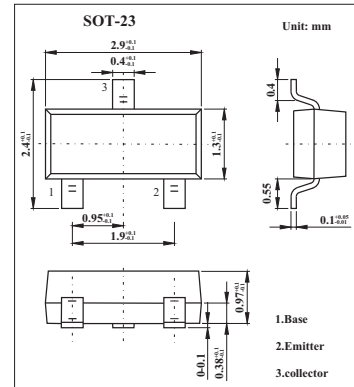


Epitaxial Planar PNP Transistor

KTA1504S-Y

■ Features

- Collector Power Dissipation: $P_C=150\text{mW}$
- Collector Current: $I_C=-150\text{mA}$

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Collector-Emitter Voltage	V_{CE0}	-50	V
Collector-Base Voltage	V_{CB0}	-50	V
Emitter-Base Voltage	V_{EB0}	-5	V
Collector Current	I_C	-150	mA
Collector Power Dissipation	P_C	150	mW
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	-55 to 150	$^\circ\text{C}$

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=-100\mu\text{A}, I_E=0$	-50			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=-1\text{mA}, I_B=0$	-50			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=-100\mu\text{A}, I_C=0$	-5			V
Collector Cut-off Current	I_{CBO}	$V_{CB}=-50\text{V}, I_E=0$			-0.1	μA
Emitter Cut-off Current	I_{EBO}	$V_{EB}=-5\text{V}, I_C=0$			-0.1	μA
DC Current Gain	h_{FE}	$V_{CE}=-6\text{V}, I_C=-2\text{mA}$	120		240	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=-100\text{mA}, I_B=-10\text{mA}$		-0.1	-0.3	V
Transition Frequency	f_T	$V_{CE}=-10\text{V}, I_C=-1\text{mA}$	80			MHz
Collector Output Capacitance	C_{ob}	$V_{CB}=-10\text{V}, I_E=0, f=1\text{MHz}$		4.0	7.0	pF
Noise Figure	NF	$V_{CE}=-6\text{V}, I_C=-0.1\text{mA}, f=1\text{kHz}, R_g=10\text{K}\Omega$		1.0	10	dB